

IN THE CLAIMS:

Please amend claims 1, 4, 10, 19, 32, 45, 68 and 71 as follows. Attached hereto is a marked-up copy of the amended claims

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C1

1. (Twice Amended) A semiconductor device comprising:
a first substrate having an insulating surface;
a second substrate opposing said first substrate;
at least one thin film transistor formed on said insulating surface, said thin film transistor having a polycrystalline semiconductor layer comprising source, drain and channel regions;
an interlayer insulating film comprising an inorganic material formed on said thin film transistor;
an organic resin film provided over said interlayer insulating film; and
a pixel electrode formed over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film,
wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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4. (Amended) A device according to claim 1 wherein said channel region comprises a material selected from the group consisting of silicon, germanium and a combination thereof.

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10. (Twice Amended) A semiconductor device comprising:
a first substrate having an insulating surface;
a second substrate opposing said first substrate;
at least one thin film transistor formed on said insulating surface, said thin film transistor having a polycrystalline semiconductor layer comprising source, drain and channel regions;
an interlayer insulating film comprising an inorganic material formed on said thin film transistor;
an organic resin film provided over said interlayer insulating film; and
a pixel electrode formed over said organic resin film and connected to said thin

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B4

film transistor through an opening provided in said organic resin film,
wherein said polycrystalline semiconductor layer exhibits a peak of Raman
spectra, displaced from 522 cm^{-1} to the lower frequency direction, and
wherein said polycrystalline semiconductor layer is formed by crystallizing an
amorphous semiconductor layer.

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19. (Twice Amended) A semiconductor device comprising:
a first substrate having an insulating surface;
a second substrate opposing said first substrate;
at least one thin film transistor formed on said insulating surface, said thin film
transistor comprising:
a polycrystalline semiconductor layer having source, drain and channel regions;
a gate insulating layer adjacent to said channel region; and
a gate electrode adjacent to said channel region;
an interlayer insulating film comprising an inorganic material formed on said thin
film transistor; and
an organic resin film provided over said interlayer insulating film;
wherein said polycrystalline semiconductor layer exhibits a peak of Raman
spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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32. (Twice Amended) A semiconductor device comprising:
a first substrate having an insulating surface;
a second substrate opposing said first substrate;
at least one thin film transistor formed on said insulating surface, said thin film
transistor comprising:
a polycrystalline semiconductor layer having source, drain and channel regions;
a gate insulating layer adjacent to said channel region;
an interlayer insulating film comprising an inorganic material formed on said thin
film transistor; and
an organic resin film provided over said thin film transistor and said interlayer
insulating film;

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wherein said polycrystalline semiconductor layer comprises silicon and exhibits a peak of Raman spectra, displaced from 522 cm^{-1} to the lower frequency direction, and

wherein said polycrystalline semiconductor layer is formed by crystallizing an amorphous semiconductor layer.

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45. (Twice Amended) A semiconductor device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least an n-channel thin film transistor and at least a p-channel thin film transistor both formed over said first substrate, each of said n-channel and p-channel thin film transistors comprising:

a polycrystalline semiconductor layer having source, drain and channel regions;

a gate insulating layer adjacent to said channel region; and

a gate electrode adjacent to said channel region;

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an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said interlayer insulating film;

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wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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68. (Amended) A semiconductor device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

a polycrystalline semiconductor layer having source, drain and channel regions;

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an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said interlayer insulating film;

a pixel electrode provided over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film;

cont
B8 wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from 522 cm^{-1} to the lower frequency direction, and

wherein said polycrystalline semiconductor layer is formed by crystallizing an amorphous semiconductor layer.

B9 71. (Amended) A device according to claim 68 wherein said channel region comprises a material selected from the group consisting of silicon, germanium and a combination thereof.
